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List of Publications by Year in descending order

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37
papers

1,161
citations

471509

17
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377865

34
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38
all docs

38
docs citations

38
times ranked

1829
citing authors

#	ARTICLE	IF	CITATIONS
1	Plasticity in memristive devices for spiking neural networks. <i>Frontiers in Neuroscience</i> , 2015, 9, 51.	2.8	188
2	Nonvolatile bipolar resistive switching in Au/BiFeO ₃ /Pt. <i>Journal of Applied Physics</i> , 2011, 109, 124117.	2.5	116
3	Exploiting Memristive BiFeO ₃ Bilayer Structures for Compact Sequential Logics. <i>Advanced Functional Materials</i> , 2014, 24, 3357-3365.	14.9	116
4	Decisive role of oxygen vacancy in ferroelectric versus ferromagnetic Mn-doped BaTiO ₃ thin films. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	112
5	Bipolar Electric-Field Enhanced Trapping and Detrapping of Mobile Donors in BiFeO ₃ Memristors. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 19758-19765.	8.0	84
6	Single pairing spike-timing dependent plasticity in BiFeO ₃ memristors with a time window of 25 ms to 125 ns. <i>Frontiers in Neuroscience</i> , 2015, 9, 227.	2.8	54
7	Key concepts behind forming-free resistive switching incorporated with rectifying transport properties. <i>Scientific Reports</i> , 2013, 3, 2208.	3.3	48
8	Effect of the substrate on the insulator-metal transition of vanadium dioxide films. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	43
9	Reduced leakage current in BiFeO ₃ thin films with rectifying contacts. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	39
10	Field-Driven Hopping Transport of Oxygen Vacancies in Memristive Oxide Switches with Interface-Mediated Resistive Switching. <i>Physical Review Applied</i> , 2018, 10, .	3.8	34
11	Mn-doped Ge and Si: A Review of the Experimental Status. <i>Materials</i> , 2010, 3, 5054-5082.	2.9	32
12	Application of pulsed laser annealing to ferromagnetic GaMnAs. <i>Physical Review B</i> , 2010, 81, .	3.2	27
13	Substrate effect on the resistive switching in BiFeO ₃ thin films. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	26
14	Hysteresis in the magnetotransport of manganese-doped germanium: Evidence for carrier-mediated ferromagnetism. <i>Physical Review B</i> , 2010, 81, .	3.2	23
15	Bipolar resistive switching in YMnO ₃ /Nb:SrTiO ₃ pn-heterojunctions. <i>Nanotechnology</i> , 2016, 27, 455201.	2.6	20
16	An Energy-Efficient, BiFeO ₃ -Coated Capacitive Switch with Integrated Memory and Demodulation Functions. <i>Advanced Electronic Materials</i> , 2016, 2, 1500352.	5.1	19
17	Anomalous Hall resistance in Ge:Mn systems with low Mn concentrations. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	18
18	Increased static dielectric constant in ZnMnO and ZnCoO thin films with bound magnetic polarons. <i>Scientific Reports</i> , 2020, 10, 6698.	3.3	17

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19	The importance of hole concentration in establishing carrier-mediated ferromagnetism in Mn doped Ge. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	16
20	Improved retention of nonvolatile bipolar BiFeO ₃ resistive memories validated by memristance measurements. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 636-639.	0.8	16
21	Memory effect of Mn ₅ Ge ₃ nanomagnets embedded inside a Mn-diluted Ge matrix. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	14
22	Role of Coulomb blockade and spin-flip scattering in tunneling magnetoresistance of FeCo-Si-O nanogranular films. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	14
23	Hysteretic anomalous Hall effect in a ferromagnetic, Mn-rich Ge:Mn nanonet. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	13
24	Novel implementation of memristive systems for data encryption and obfuscation. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	11
25	Wafer-level uniformity of atomic-layer-deposited niobium nitride thin films for quantum devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, 052401.	2.1	11
26	Electroforming-free resistive switching in yttrium manganite thin films by cationic substitution. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	9
27	Microstructure, electrical, magnetic, and extraordinary Hall effect studies in Ni:SiO ₂ nanogranular films synthesized by atom beam sputtering. <i>Journal of Applied Physics</i> , 2010, 107, .	2.5	8
28	Transport in ZnCoO thin films with stable bound magnetic polarons. <i>APL Materials</i> , 2014, 2, .	5.1	6
29	Transition metal diffusion in diluted magnetic Si and GaAs prepared by pulsed laser processing. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	5
30	Electroforming-free resistive switching in polycrystalline YMnO ₃ thin films. <i>Journal of Applied Physics</i> , 2018, 124, .	2.5	5
31	Charged domains in ferroelectric, polycrystalline yttrium manganite thin films resolved with scanning electron microscopy. <i>Nanotechnology</i> , 2020, 31, 31LT01.	2.6	4
32	Voigt effect measurement on PLD grown NiO thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 334-337.	0.8	3
33	Tunable large field magnetoconductance of ZnO, ZnMnO, and ZnCoO thin films. <i>Journal of Applied Physics</i> , 2019, 125, 215305.	2.5	3
34	Prospects for application of ferroelectric manganites with controlled vortex density. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	3
35	Thouless length and valley degeneracy factor of ZnMnO thin films with anisotropic, highly conductive surface layers. <i>Journal of Applied Physics</i> , 2017, 121, .	2.5	2
36	Electrochemical growth mechanism of nanoporous platinum layers. <i>Communications Chemistry</i> , 2021, 4, .	4.5	2

#	ARTICLE	IF	CITATIONS
37	Analysis of Low-Temperature Magnetotransport Properties of NbN Thin Films Grown by Atomic Layer Deposition. Magnetochemistry, 2022, 8, 33.	2.4	0